

This cross-sectional view shows a semiconductor device with a patterned layer 195. The device includes a substrate 170, a base layer 155, and a patterned layer 195. The patterned layer 195 is composed of a top layer 180 and a bottom layer 160. The top layer 180 is a thin layer with a diagonal hatching pattern, and the bottom layer 160 is a thicker layer with a diagonal hatching pattern. The patterned layer 195 is formed in a series of rectangular blocks. The top layer 180 is formed on the bottom layer 160, and the bottom layer 160 is formed on the base layer 155. The base layer 155 is formed on the substrate 170. The substrate 170 is a thick layer with a diagonal hatching pattern.

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FIG. 1C.
(PRIOR ART)

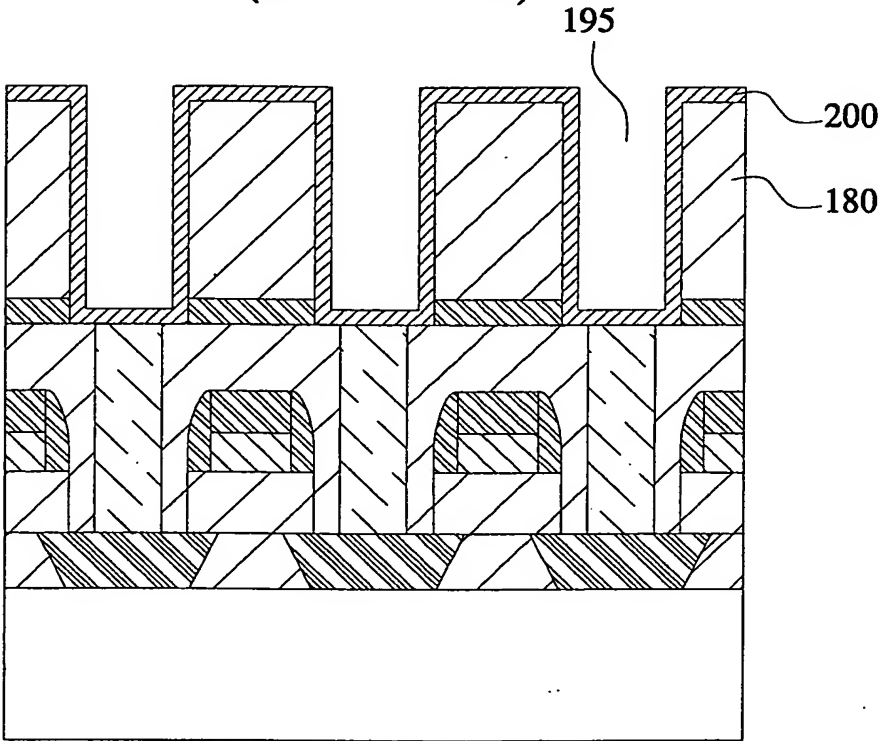
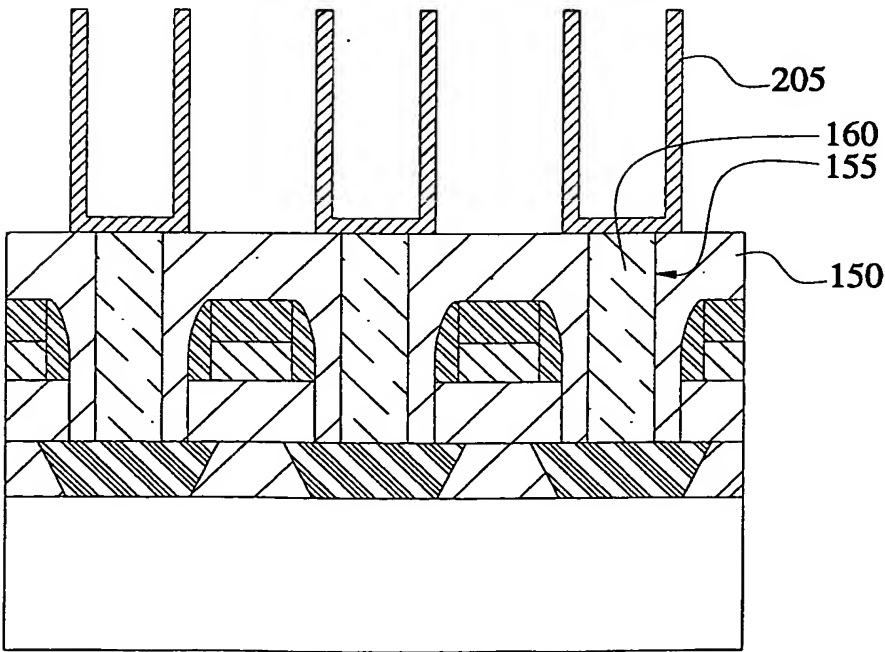


FIG. 1D
(PRIOR ART)



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FIG. 2A.

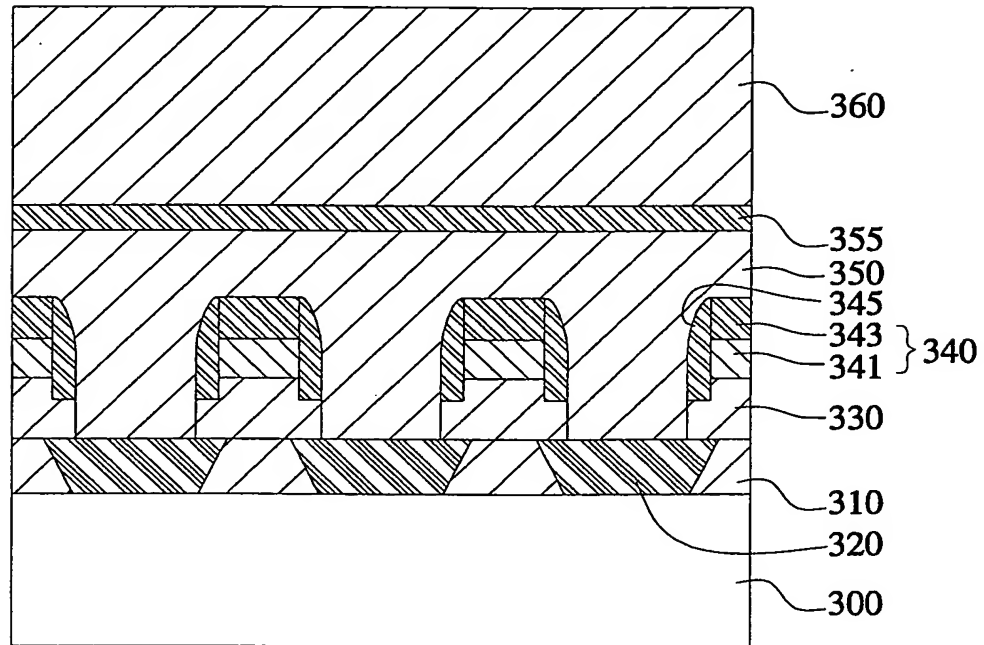
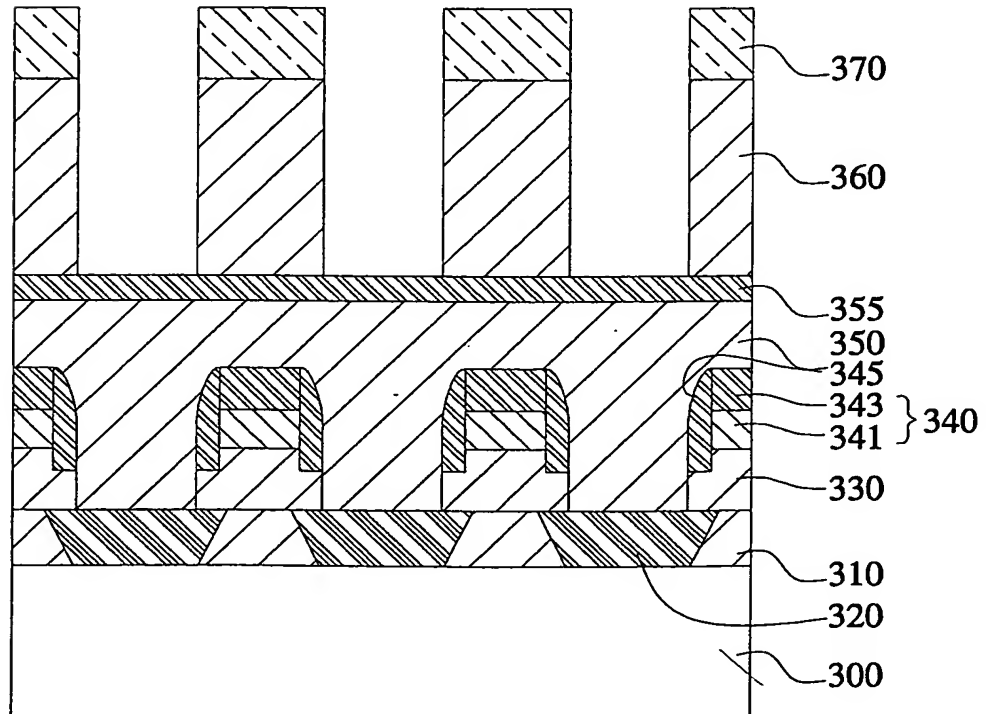


FIG. 2B



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FIG. 2C

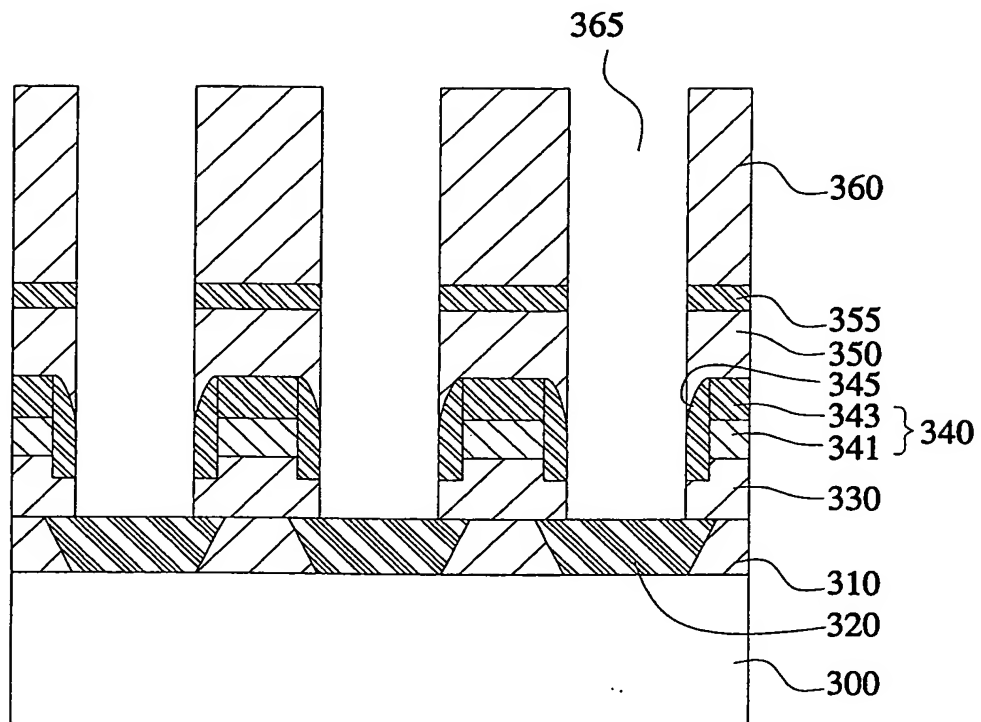
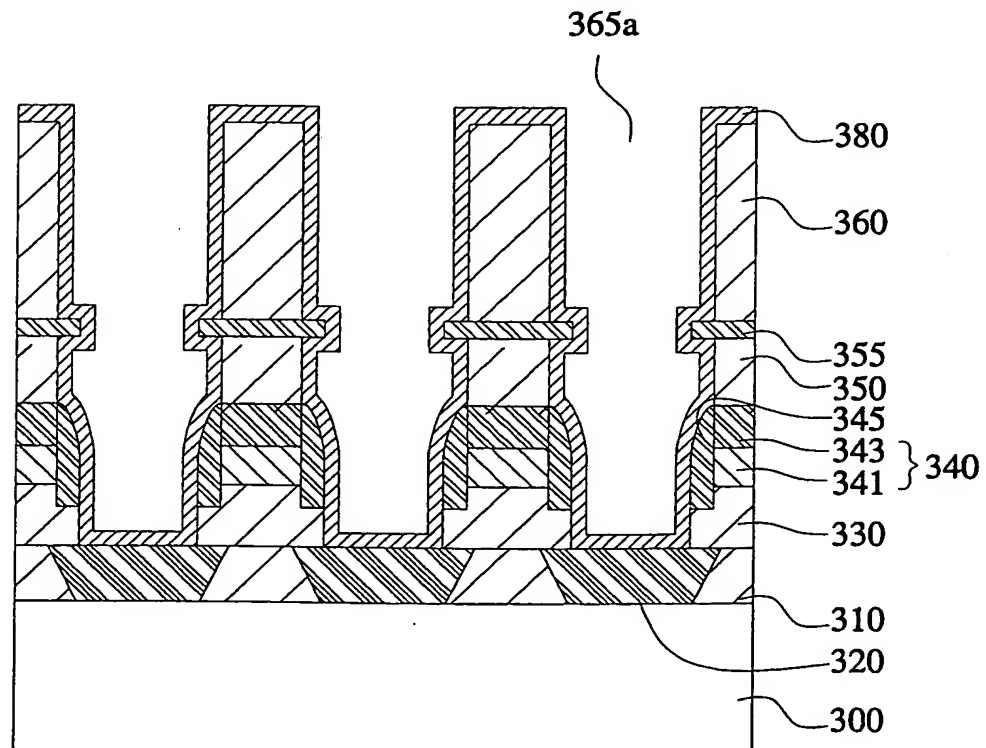


FIG. 2D



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FIG. 2E.

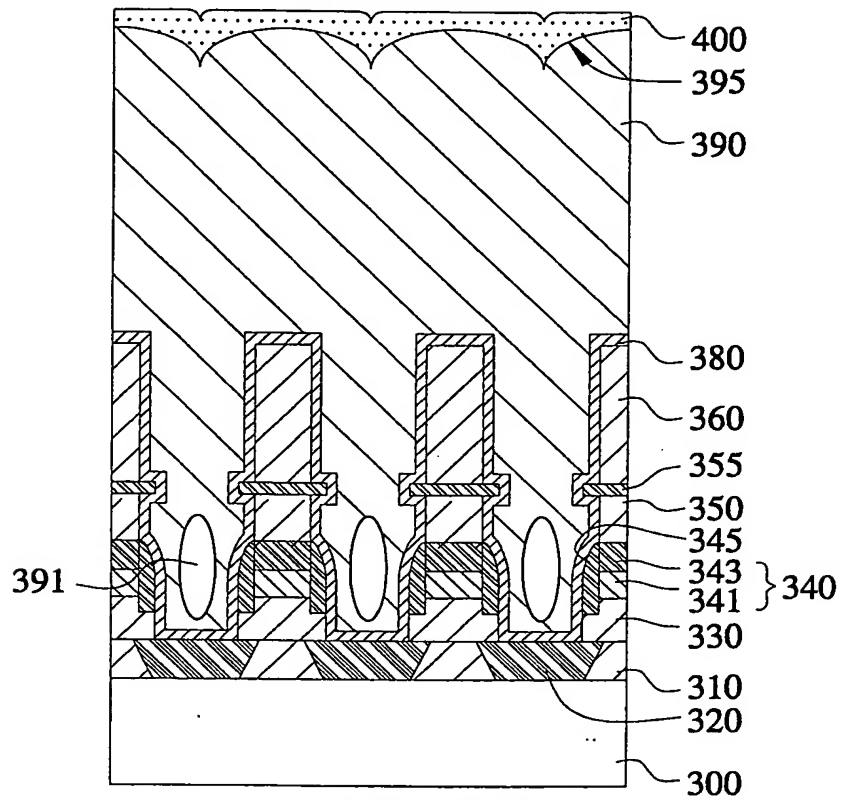
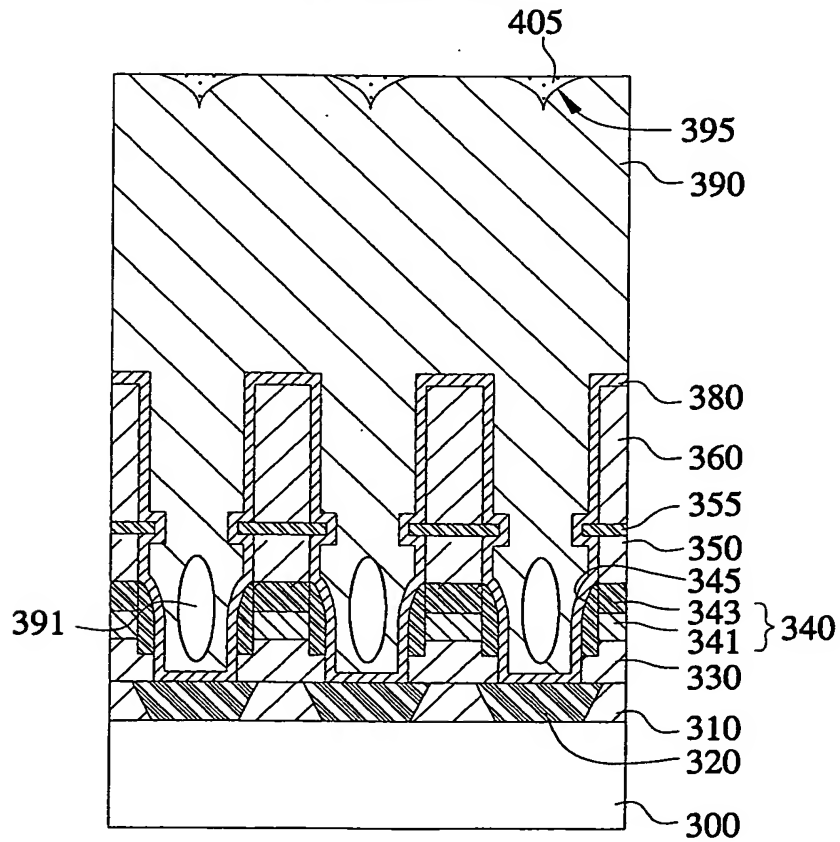
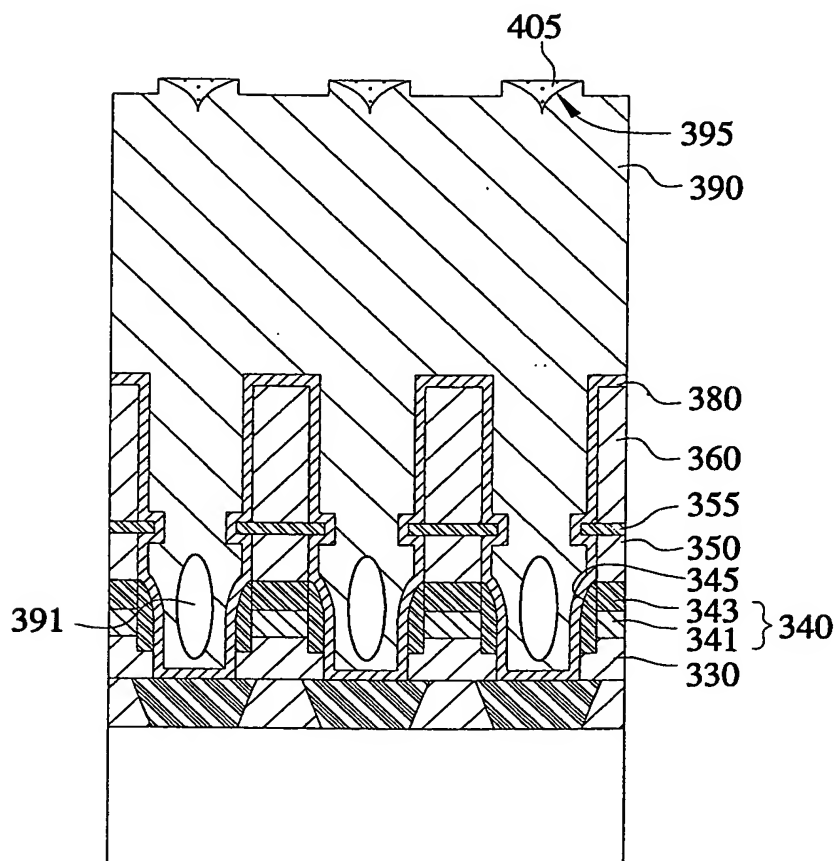


FIG. 2F

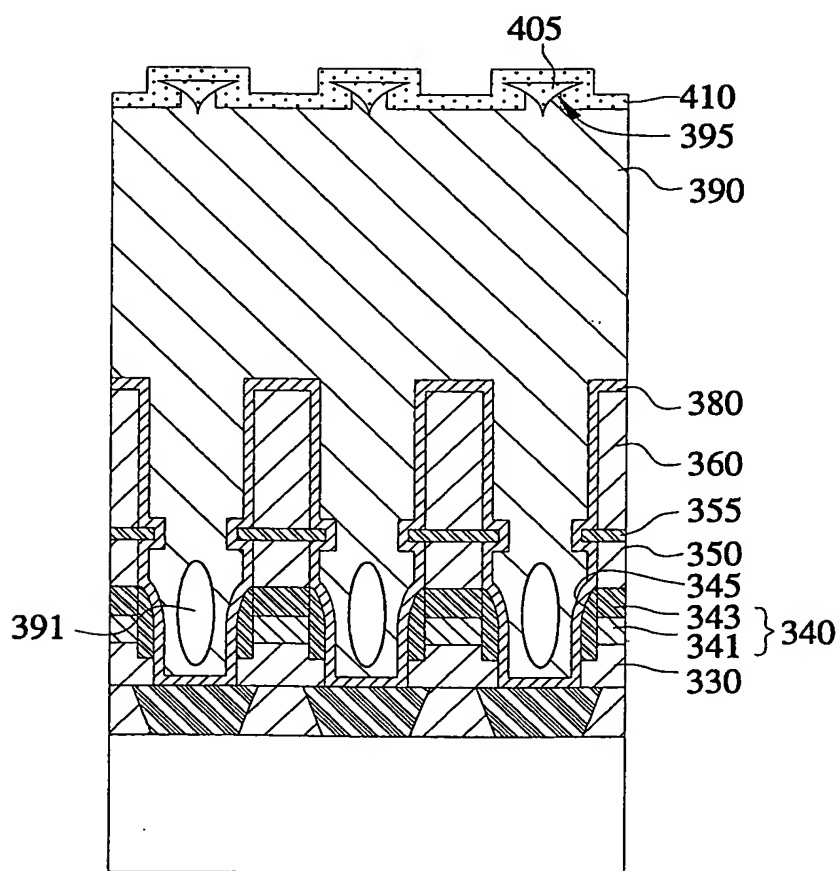


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FIG. 2G.

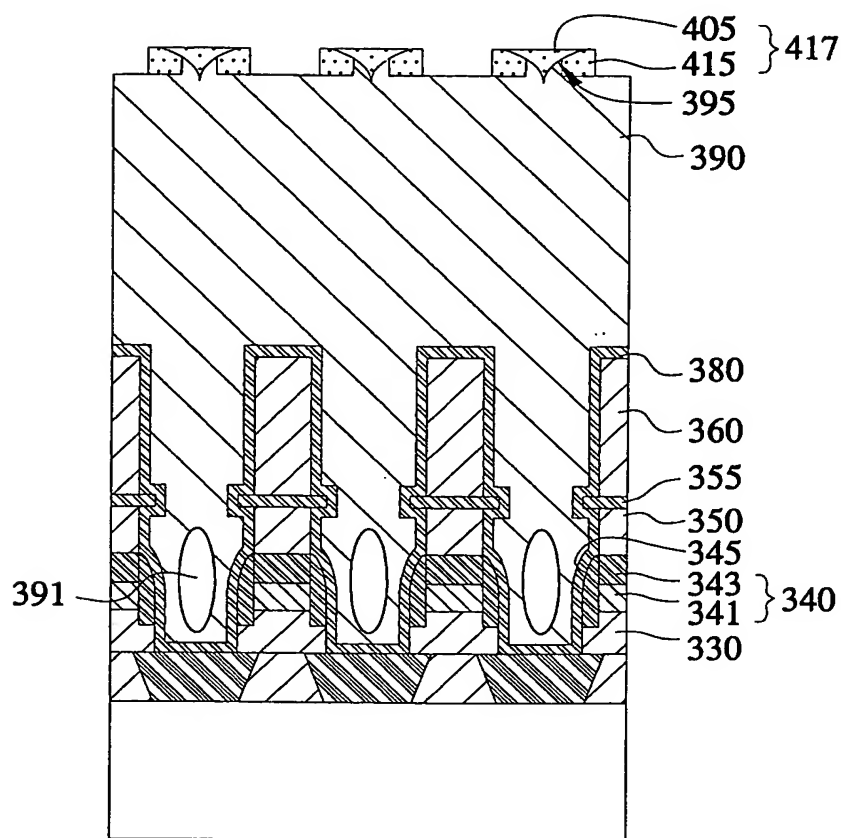


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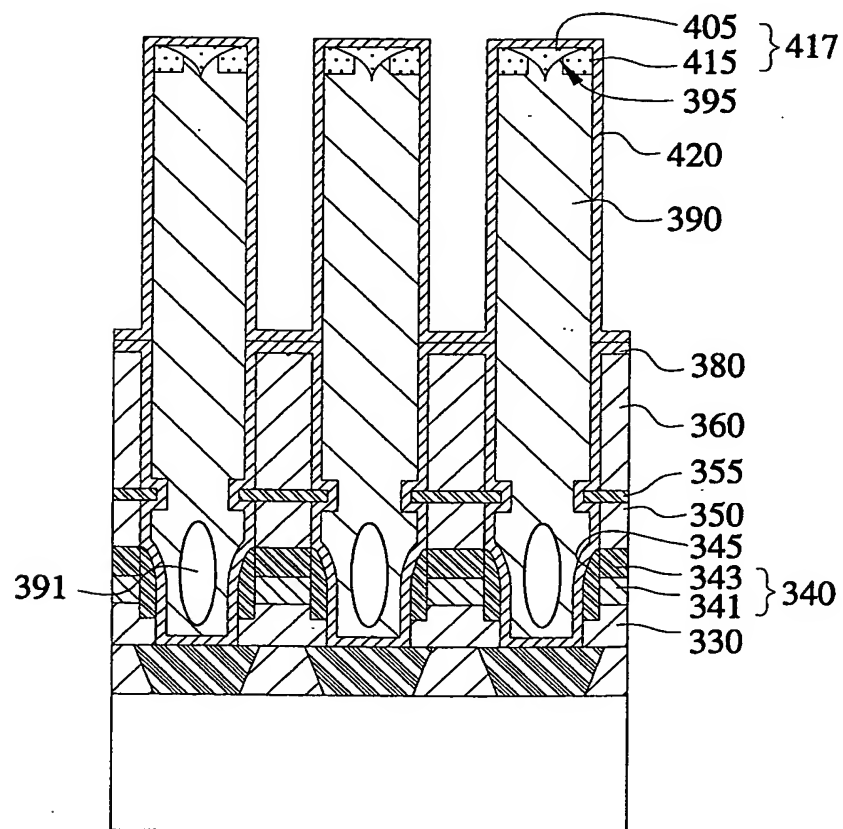
FIG. 2H



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FIG. 2I

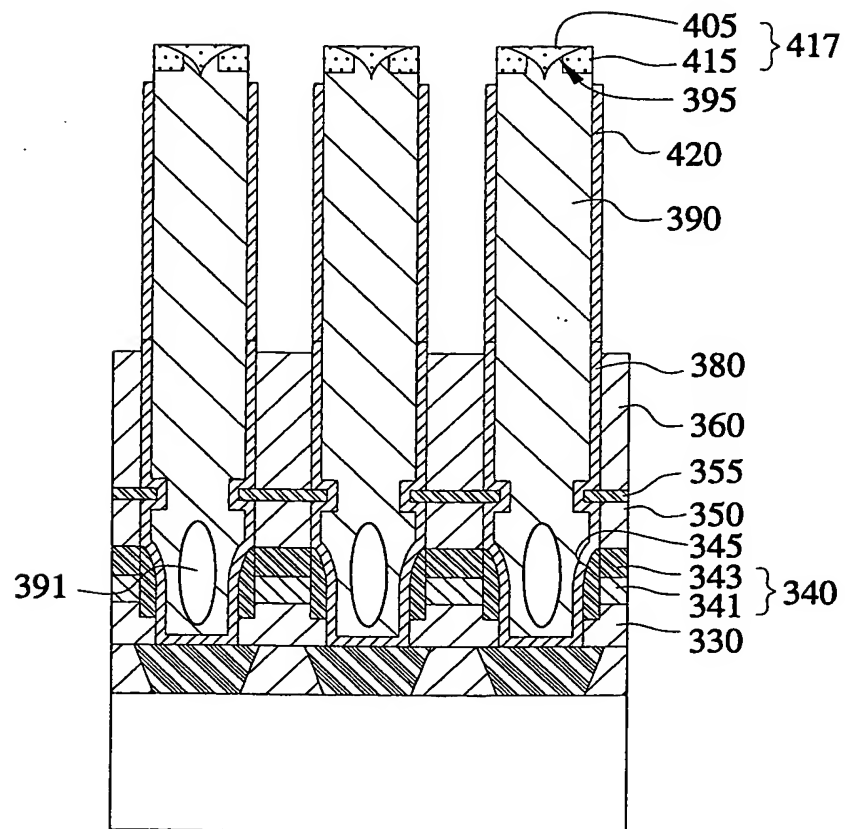


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FIG. 2J



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FIG. 2K



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FIG. 2L

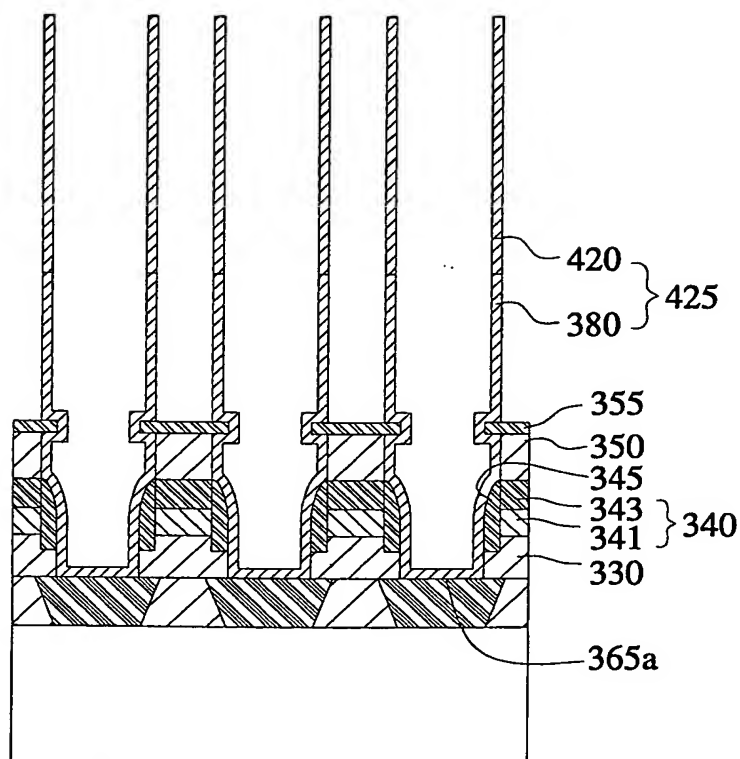


FIG. 3A

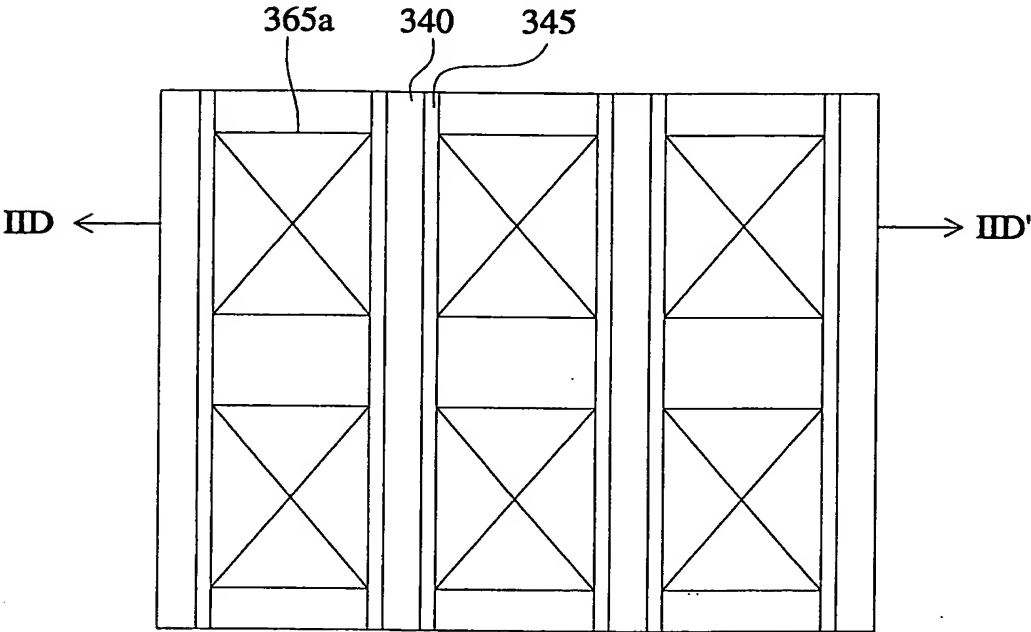
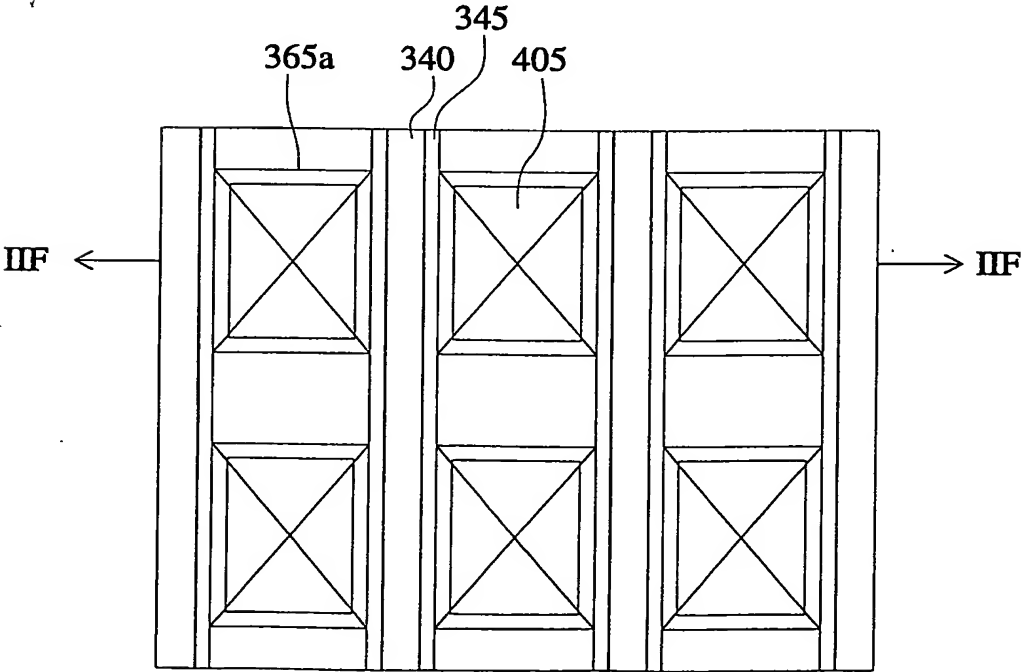


FIG. 3B



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FIG. 3C

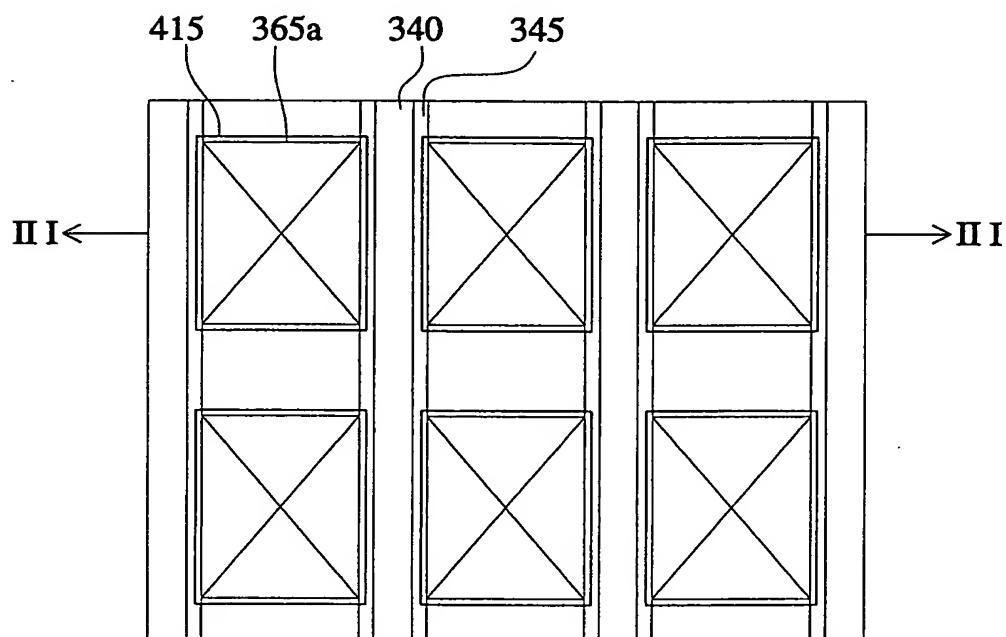


FIG. 3D

